



Low-Voltage Dual SPST Analog Switch

DESCRIPTION

The DG9232, 9233 is a single-pole/single-throw monolithic CMOS analog device designed for high performance switching of analog signals. Combining low power, high speed (t_{ON}: 35 ns, t_{OFF}: 20 ns), low on-resistance (R_{DS(on)}: 20 Ω) and small physical size, the DG9232, 9233 is ideal for portable and battery powered applications requiring high performance and efficient use of board space.

The DG9232, 9233 is built on Vishay Siliconix's low voltage BCD-15 process. Minimum ESD protection, per method 3015.7 is 2000 V. An epitaxial layer prevents latchup. Break-before -make is guaranteed for DG9232. 9233.

Each switch conducts equally well in both directions when on, and blocks up to the power supply level when off.

BENEFITS

- Reduced power consumption
- Simple logic interface
- High accuracy
- Reduce board space

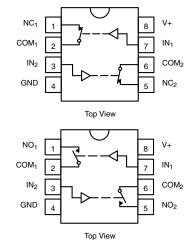
FEATURES

- Low voltage operation (+ 2.7 V to + 5 V)
- Low on-resistance R_{DS} (on): 20 Ω
- Fast switching t_{ON}: 35 ns, t_{OFF}: 20 ns
- Low leakage I_{COM(on)}: 200 pA max.
- Low charge injection Q_{INJ}: 1 pC
- Low power consumption
- TTL/CMOS compatible
- ESD protection > 2000 V (method 3015.7)
- Available in MSOP-8 and SOIC-8
- Compliant to RoHS Directive 2002/95/EC

APPLICATIONS

- Battery operated systems
- Portable test equipment
- Sample and hold circuits
- Cellular phones
- Communication systems
- Military radio
- PBX, PABX guidance and control systems

FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION



TRUTH TABLE - DG9232			
Logic	Switch		
0	On		
1	Off		

Logic "0" ≤ 0.8 V Logic "1" ≥ 2.4 V

TRUTH TABLE - DG9233			
Logic	Switch		
0	Off		
1	On		

Logic "0" ≤ 0.8 V Logic "1" ≥ 2.4 V

DERING INFORMATION			
Temp Range	Package	Part Number	
		DG9232DY	
		DG9232DY-E3	
		DG9232DY-T1	
	SOIC-8	DG9232DY-T1-E3	
- 40 °C to 85 °C		DG9233DY	
- 40 °C 10 85 °C		DG9233DY-E3	
		DG9233DY-T1	
		DG9233DY-T1-E3	
	MSOP-8	DG9232DQ-T1-E3	
	IVISOP-0	DG9233DQ-T1-E3	

^{*} Pb containing terminations are not RoHS compliant, exemptions may apply

DG9232, DG9233

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ABSOLUTE MAXIMUM RATINGS				
Parameter		Limit	Unit	
Reference V+ to GND	- 0.3 to + 13			
IN, COM, NC, NO ^a	- 0.3 to (V+ + 0.3)	V		
Continuous Current (Any terminal)	± 20	mA		
Peak Current (Pulsed at 1 ms, 10 % duty cy	± 40	MA		
ESD (Method 3015.7)		> 2000	V	
Storage Temperature	D suffix	- 65 to 125	°C	
Power Dissipation (Packages) ^b	8-pin narrow body SOIC ^c	400	mW	

Notes:

- a. Signals on NC, NO, or COM or IN exceeding V+ will be clamped by internal diodes. Limit forward diode current to maximum current ratings.
- b. All leads welded or soldered to PC board.
- c. Derate 6.5 mW/°C above 70 °C.

		Test Conditions		D Suffix - 40 °C to 85 °C			
		Otherwise Unless Specified		-			
Parameter	Symbol	$V+ = 3 V$, $\pm 10 \%$, $V_{IN} = 0.8 V$ or 2.4 V^e	Temp.a	Min. ^c	Typ.b	Max.c	Uni
Analog Switch							_
Analog Signal Range ^d	V _{ANALOG}		Full	0		3	V
Drain-Source On-Resistance	R _{DS(on)}	V_{NO} or $V_{NC} = 1.5 \text{ V}, \text{ V+} = 2.7 \text{ V}$ $I_{COM} = 5 \text{ mA}$	Room Full		30	50 80	
R _{DS(on)} Match ^d	$\Delta R_{DS(on)}$	V_{NO} or $V_{NC} = 1.5 \text{ V}$	Room		0.4	2	Ω
R _{DS(on)} Flatness ^d	R _{DS(on)} Flatness	V _{NO} or V _{NC} = 1 and 2 V	Room		4	8	
NO or NC Off Leakage Current ^g	I _{NO/NC(off)}	V_{NO} or $V_{NC} = 1 \text{ V/2 V}$, $V_{COM} = 2 \text{ V/1 V}$	Room Full	- 100 - 5000	5	100 5000	
COM Off Leakage Current ^g	I _{COM(off)}	$V_{COM} = 1 \text{ V/2 V}, V_{NO} \text{ or } V_{NC} = 2 \text{ V/1 V}$	Room Full	- 100 - 5000	5	100 5000	pА
Channel-On Leakage Current ^g	I _{COM(on)}	$V_{COM} = V_{NO}$ or $V_{NC} = 1 \text{ V/2 V}$	Room Full	- 200 - 10000	10	200 10000	
Digital Control							
Input Current	I _{INL} or I _{INH}		Full		1		μΑ
Dynamic Characteristics							
Turn-On Time	t _{ON}	V_{NO} or $V_{NC} = 1.5 \text{ V}$	Room Full		50	120 200	ns
Turn-Off Time	t _{OFF}	ANO 01 ANG = 1.9 A	Room Full		20	50 120	115
Charge Injection ^d	Q _{INJ}	$C_L = 1 \text{ nF, } V_{GEN} = 0 \text{ V, } R_{GEN} = 0 \Omega$	Room		1	5	рС
Off-Isolation	OIRR	$R_1 = 50 \Omega$, $C_1 = 5 pF$, $f = 1 MHz$	Room		- 74		dB
Crosstalk	X _{TALK}	11L - 30 sz, OL - 3 pi , i - 1 Wil 12	Room		- 90		ub
NC and NO Capacitance	C _{S(off)}		Room		7		
Channel-On Capacitance	C _{COM(on)}	f = 1 MHz	Room		20		pF
COM-Off Capacitance	C _{COM(off)}		Room		13		1
Power Supply	, , , ,						
Positive Supply Range	V+			2.7		12	V
Power Supply Current	I+	$V+ = 3.3 \text{ V}, V_{IN} = 0 \text{ or } 3.3 \text{ V}$				1	μΑ

Notes:

- a. Room = 25 $^{\circ}$ C, Full = as determined by the operating suffix.
- b. Typical values are for design aid only, not guaranteed nor subject to production testing.
- c. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this datasheet.
- d. Guarantee by design, nor subjected to production test.
- e. V_{IN} = input voltage to perform proper function.
- f. Difference of min and max values.
- g. Guaranteed by 5 V leakage tests, not production tested.



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		Test Conditions Otherwise Unless Specified		D Suffix - 40 °C to 85°C			
Parameter	Symbol	$V+ = 5 V$, $\pm 10 \%$, $V_{IN} = 0.8 V$ or 2.4 V^e	Temp.a	Min.c	Typ.b	Max.c	Unit
Analog Switch				l .		l	
Analog Signal Range ^d	V _{ANALOG}		Full	0		5	V
Drain-Source On-Resistance	R _{DS(on)}	V_{NO} or $V_{NC} = 3.5 \text{ V}, \text{ V+} = 4.5 \text{ V}$ $I_{COM} = 5 \text{ mA}$	Room Full		20	30 50	
R _{DS(on)} Match ^d	$\Delta R_{DS(on)}$	V_{NO} or $V_{NC} = 3.5 \text{ V}$	Room		0.4	2	Ω
R _{DS(on)} Flatness ^d	R _{DS(on)} Flatness	V_{NO} or $V_{NC} = 1, 2$ and 3 V	Room		2	6	
NO or NC Off Leakage Current ^g	I _{NO/NC(off)}	V_{NO} or V_{NC} = 1 V/4 V, V_{COM} = 4 V/1 V	Room Full	- 100 - 5000	10	100 5000	
COM Off Leakage Current	I _{COM(off)}	$V_{COM} = 1 \text{ V/4 V}, V_{NO} \text{ or } V_{NC} = 4 \text{ V/1 V}$	Room Full	- 100 - 5000	10	100 5000	pΑ
Channel-On Leakage Current	I _{COM(on)}	$V_{COM} = V_{NO} \text{ or } V_{NC} = 1 \text{ V/4 V}$	Room Full	- 200 - 10000		200 10000	
Digital Control			•			•	
Input Current	I _{INL} or I _{INH}		Full		1		μ۵
Dynamic Characteristics							
Turn-On Time	t _{ON}	V_{NO} or $V_{NC} = 3.0 \text{ V}$	Room Full		35	75 150	ns
Turn-Off Time	t _{OFF}	NO NO	Room Full		20	50 100	7 113
Charge Injection ^d	Q _{INJ}	C_L = 1 nF, V_{GEN} = 0 V, R_{GEN} = 0 Ω	Room		2	5	рC
Off-Isolation	OIRR	$R_1 = 50 \Omega, C_1 = 5 pF, f = 1 MHz$	Room		- 74		dB
Crosstalk	X _{TALK}	11 = 30 32, 31 = 3 p1, 1 = 1 141112	Room		- 90		uL
NC and NO Capacitance	C _(off)		Room		7		
Channel-On Capacitance	C _{D(on)}	f = 1 MHz	Room		20		рF
COM-Off Capacitance	C _{D(off)}		Room		13		
Power Supply							
Positive Supply Range	V+			2.7		12	V
Power Supply Current	I+	V+ = 5.5 V, V _{IN} = 0 or 5.5 V	<u> </u>			1	μΑ

Notes:

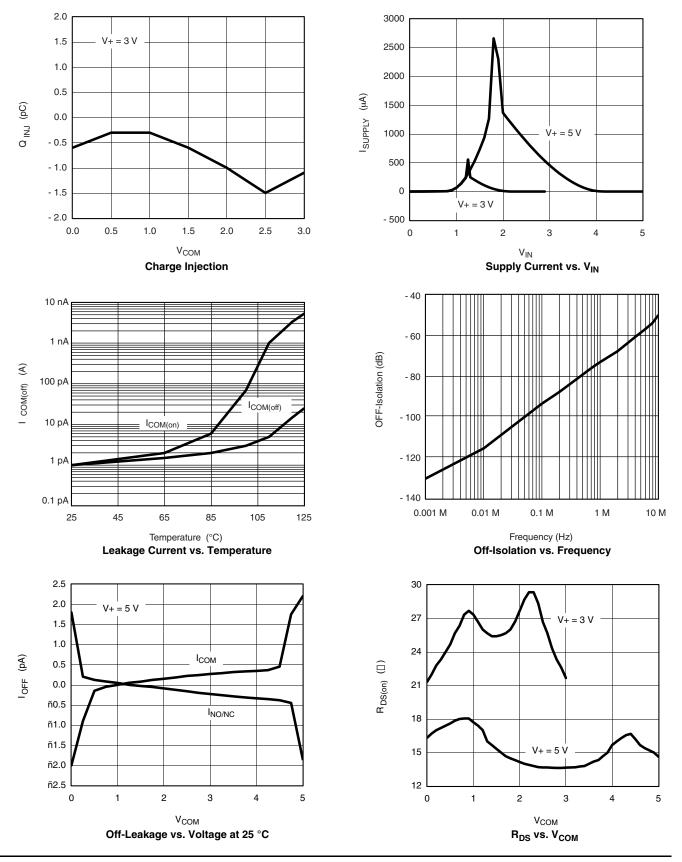
- a. Room = 25 °C, Full = as determined by the operating suffix.
 b. Typical values are for design aid only, not guaranteed nor subject to production testing.
- c. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this datasheet.
- d. Guarantee by design, nor subjected to production test.
- e. V_{IN} = input voltage to perform proper function.
- f. Difference of min and max values.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

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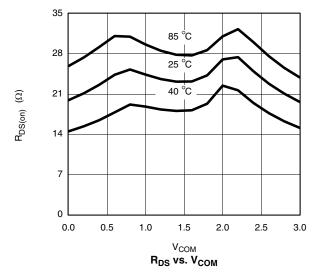


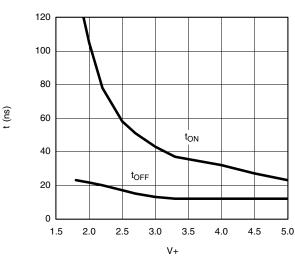
TYPICAL CHARACTERISTICS $T_A = 25$ °C, unless otherwise noted



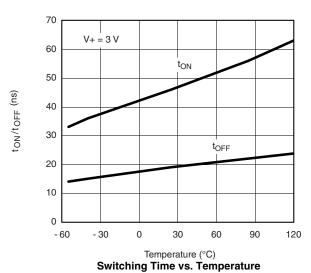


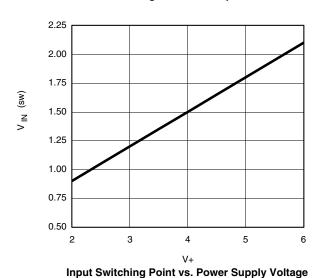
TYPICAL CHARACTERISTICS $T_A = 25$ °C, unless otherwise noted





t_{ON/tOFF} vs. Power Supply Voltage

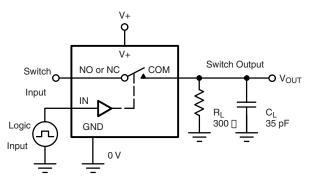




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TEST CIRCUITS

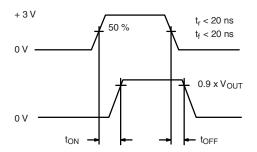




Switch Output

Logic

Input



C_L (includes fixture and stray capacitance)

$$V_{OUT} = V_{COM} \left(\frac{R_L}{R_L + R_{ON}} \right)$$

Logic "1" = Switch On Logic input waveforms inverted for switches that have the opposite logic sense.

Figure 1. Switching Time

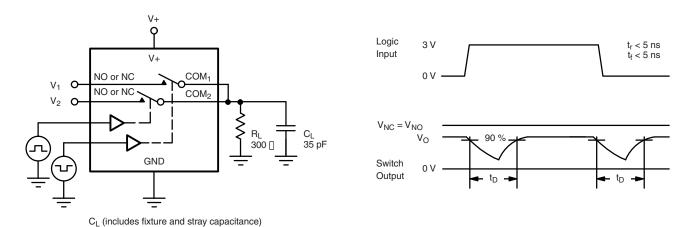
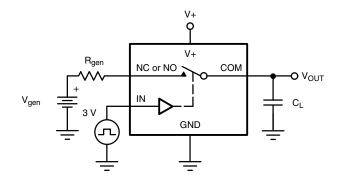
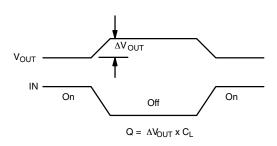


Figure 2. Break-Before-Make Interval





IN depends on switch configuration: input polarity determined by sense of switch.

Figure 3. Charge Injection



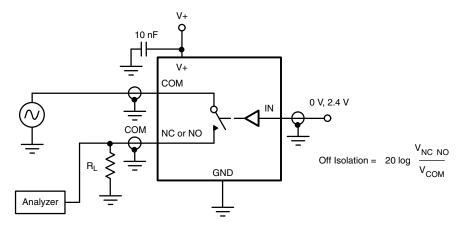


Figure 4. Off-Isolation

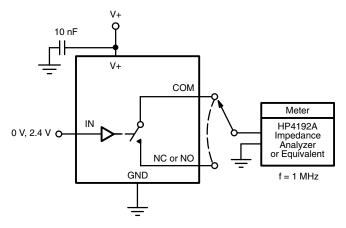


Figure 5. Channel Off/On Capacitance

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SOIC (NARROW): 8-LEAD JEDEC Part Number: MS-012







	MILLIM	IETERS	INCHES		
DIM	Min	Max	Min	Max	
Α	1.35	1.75	0.053	0.069	
A ₁	0.10	0.20	0.004	0.008	
В	0.35	0.51	0.014	0.020	
С	0.19	0.25	0.0075	0.010	
D	4.80	5.00	0.189	0.196	
Е	3.80	4.00	0.150	0.157	
е	1.27 BSC		0.050 BSC		
Н	5.80	6.20	0.228	0.244	
h	0.25	0.50	0.010	0.020	
L	0.50	0.93	0.020	0.037	
q	0°	8°	0°	8°	
S	0.44	0.64	0.018	0.026	
ECN: C-06527-Rev. I. 11-Sep-06					

DWG: 5498

Document Number: 71192 www.vishay.com 11-Sep-06

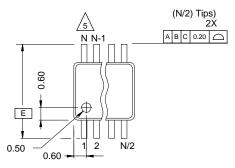




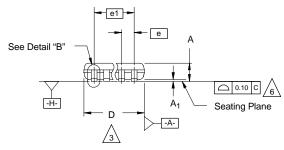


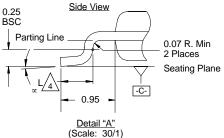
MSOP: 8-LEADS

JEDEC Part Number: MO-187, (Variation AA and BA)



Top View





NOTES:

. Die thickness allowable is 0.203 ± 0.0127 .

2. Dimensioning and tolerances per ANSI.Y14.5M-1994.



Dimensions "D" and "E $_1$ " do not include mold flash or protrusions, and are measured at Datum plane $\overline{-H_2}$, mold flash or protrusions shall not exceed 0.15 mm per side.



Dimension is the length of terminal for soldering to a substrate.



Terminal positions are shown for reference only.



Formed leads shall be planar with respect to one another within 0.10 mm at seating plane.



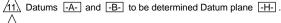
The lead width dimension does not include Dambar protrusion. Allowable Dambar protrusion shall be 0.08 mm total in excess of the lead width dimension at maximum material condition. Dambar cannot be located on the lower radius or the lead foot. Minimum space between protrusions and an adjacent lead to be 0.14 mm. See detail "B" and Section "C-C".



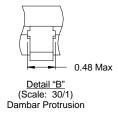
Section "C-C" to be determined at 0.10 mm to 0.25 mm from the lead tip.

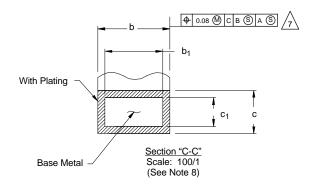
9. Controlling dimension: millimeters.

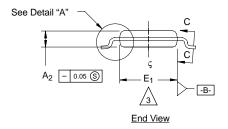
10. This part is compliant with JEDEC registration MO-187, variation AA and BA.



Exposed pad area in bottom side is the same as teh leadframe pad size.







N = 8L

	MI				
Dim	Min	Nom	Max	Note	
Α	-	-	1.10		
A ₁	0.05	0.10	0.15		
A ₂	0.75	0.85	0.95		
b	0.25	-	0.38	8	
b ₁	0.25	0.30	0.33	8	
С	0.13	-	0.23		
c ₁	0.13	0.15	0.18		
D		3.00 BSC			
Е		4.90 BSC			
E ₁	2.90	3.00	3.10	3	
е		0.65 BSC			
e ₁		1.95 BSC			
L	0.40	0.55	0.70	4	
N	8			5	
œ	0°	4°	6°		
ECN: T-02080—Rev. C, 15-Jul-02 DWG: 5867					

12-Jul-02

Document Number: 71244



RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads Dimensions in Inches/(mm)

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